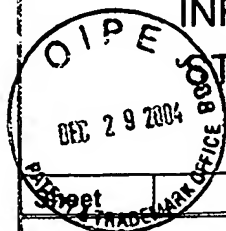


Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/750,061
Filing Date	December 30, 2003
First Named Inventor:	Justin K. Brask et al.
Art Unit	2815
Examiner Name	Fenty, Jesse A.
Attorney Docket Number	42P16680

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
WL		EP	0 623 963	A1	11/9/1994	Siemens AG		
WL		WO	02/43151	A	5/30/2002	Hitachi ULSI Sys Co Ltd		

Examiner Signature	<i>W. A. Fenty</i>	Date Considered	3/17/05
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			Examiner Name	Fenty, Jesse A.	
Sheet	2	of	2	Attorney Docket Number	42P16680
NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			T ²
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Walter J. Zumbach 3/17/2005